

EEE-2103: Electronic Devices and Circuits

Dept. of Computer Science and Engineering
University of Dhaka

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Course Outline

Syllabus:

Semiconductors: properties, bonds and types

pn junction diode: formation, properties and characteristics

Special Purpose Diodes: LED and Zener diode

Diode Applications: rectifiers, filters, clipping/clamping ckts, voltage regulator ckts

BJT: *npn/pnp* transistors, characteristics (CB/CE/CC), load line analysis

BJT Biasing: transistor parameters, stability factor, methods, analysis and design

Single Stage Amplifier: amplifier ckts, equivalent ckts, load line analysis, gain, classification

FET: classification, construction, operation and characteristics of JFET and MOSFET, transfer characteristics and DC biasing of JFET.

Power Electronics: operations, characteristics and applications of SCR, TRIAC and DIAC

Feedback Techniques and Op-amps: negative and positive feedback, inverting, non-inverting, differentiators, summing amplifiers

Oscillators: theory and characteristics

Introduction to IC fabrication.

Course Outline

Reference Books:

- (1) Electronic Devices and Circuits; David A. Bell
- (2) Electronic Devices and Circuit Theory; R. Boylestad and L. Nashelsky
- (3) Electronic Devices; Thomas L. Floyd

Class Hour:

Sunday: 08.30am ~ 10.00am

Monday: 08.30am ~ 10.00am

Place:

Room #413, Dept. of CSE, DU

Incourse Exam:

Only one compulsory incourse exam will be taken.

6 short answer type questions will be given from any consecutive 6 lectures.

Students have to answer any 5 questions in 1 hour (marks- $5 \times 5 = 25$).

Course Outline

Notices:

Available at- sazzadmsi.webnode.com

Class code @google-classroom- **6huewmh**

Marks Distribution:

(1) Attendance/Assignment: 5

(2) Incourse: 25

(3) Final: 70 (answer any 5 out of 7; $5 \times 14 = 70$; 3 hours)

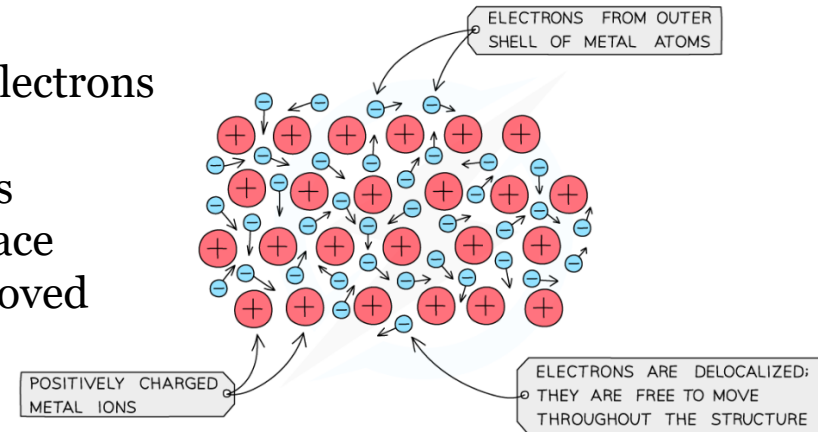
Conductors, Semiconductors and Insulators

Bonding forces between atoms:

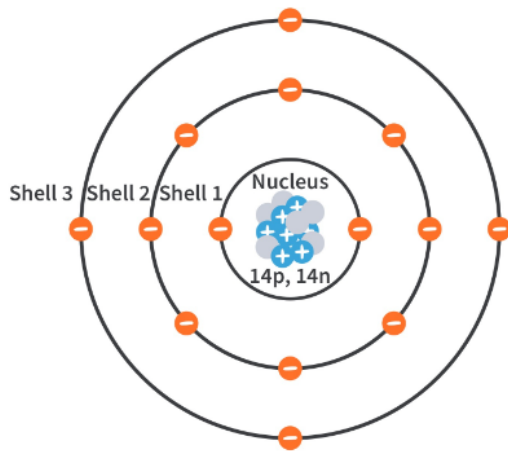
Atoms bond themselves → what happens to outer-shell electrons

- 1) Metallic bonding → easily detached valence electrons
electron gas drifting about in space
voltage → electrons are easily moved
create current flow

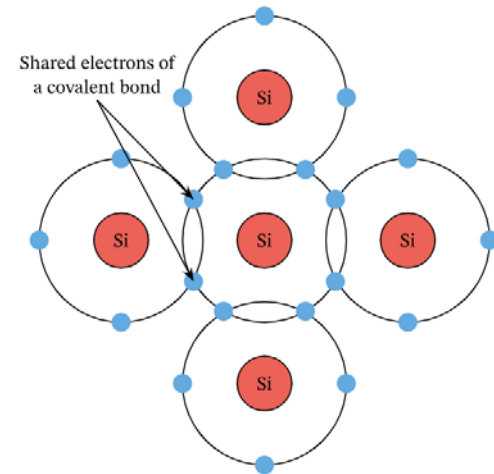
Na, Cu, Fe, Al, Au



- 2) Covalent bonding → outer shell – 4 electrons, 4 holes
valence shell electrons fill valence holes of 4 adjacent atoms
no holes, no electrons drifting about
voltage → weakly attached electrons break away
create current flow



Si, Ge, GaAs, InP



Conductors, Semiconductors and Insulators

Bonding forces between atoms:

3) Ionic bonding →

insulating materials →

rubber, glass, ceramic, wood

i) covalent bonding =

strongly attached valence shell electrons

ii) ionized atoms =

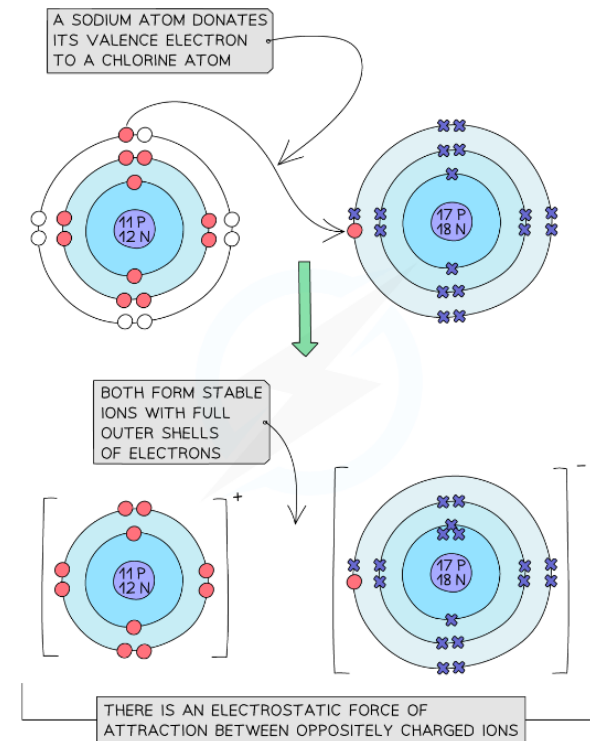
free outer-shell electrons are
accepted by nearby atoms

no free electrons to create current

Metallic bond → Conductors

Covalent bond → Semiconductors

Ionic bond → Insulators

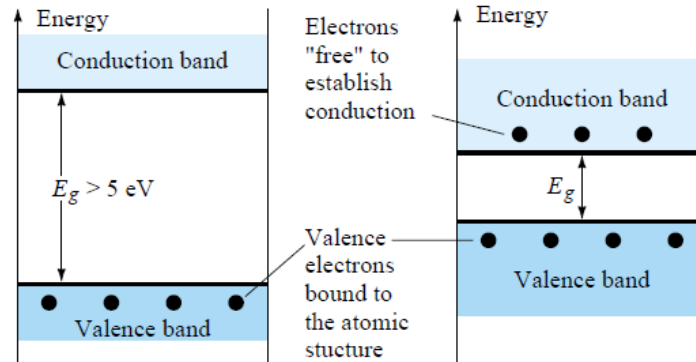


Conductors, Semiconductors and Insulators

Energy bands in different materials:

1) Insulators ($10^{14} \Omega$):

Empty conduction band
Filled valence band
Wide forbidden gap



Insulator

2) Semiconductors (10Ω):

narrower forbidden gap
At absolute zero \rightarrow

semiconductor = insulator

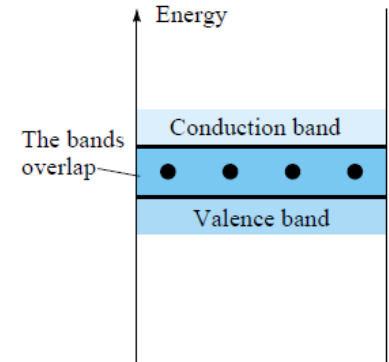
At room temperature or

Applied voltage \rightarrow

electron movement in conduction band and
hole transfer in valence band

$E_g = 1.1 \text{ eV (Si)}$
 $E_g = 0.67 \text{ eV (Ge)}$
 $E_g = 1.41 \text{ eV (GaAs)}$

Semiconductor



Conductor

3) Conductors ($10^{-6} \Omega$):

no forbidden gap

valence and conduction energy bands overlap

***n*-Type and *p*-Type Semiconductors**

Doping:

Pure semiconductor = **intrinsic material** [Si, Ge, GaAs, InP]

Intrinsic material + Impurity atoms →

improve conductivity

doping = **extrinsic material**

donor doping = generates free conduction band electrons

acceptor doping = generates valence band holes

n-type material:

Semiconductor atoms = 4 electrons + 4 holes

Impurity atoms = 5 electrons + 3 holes = pentavalent atoms

P, As, Sb, Bi

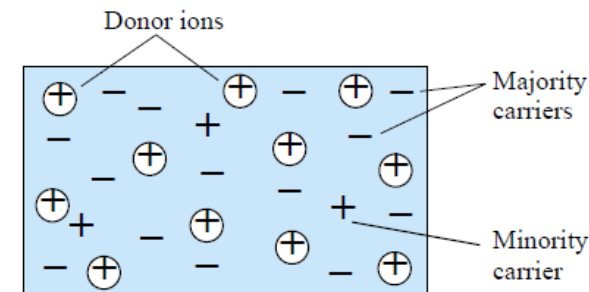
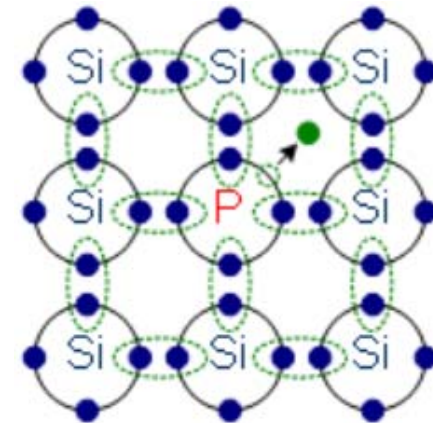
Semiconductor atoms + Impurity atoms = additional free electrons donated

n-type material
electrically neutral

Conduction = electron motion

Majority charge carriers = electrons

Minority charge carriers = holes



***n*-Type and *p*-Type Semiconductors**

p-type material:

Semiconductor atoms = 4 electrons + 4 holes

Impurity atoms = 3 electrons + 5 holes = trivalent atoms

B, Al, Ga

Semiconductor atoms + Impurity atoms = additional hole to accept electron

p-type material
electrically neutral

Conduction = hole transfer

Majority charge carriers = holes

Minority charge carriers = electrons

Electron-hole pair generation → energy creates pair of electron and hole

Electron-hole pair recombination → electron falls into hole

